

### ABSTRACT OF THE DISCLOSURE

A semiconductor light emitting element, manufacturing method thereof, integrated semiconductor light emitting device, manufacturing method thereof, illuminating device, and manufacturing method thereof are provided.

5           An n-type GaN layer is grown on a sapphire substrate, and a growth mask of SiN, for example, is formed thereon. On the n-type GaN layer exposed through an opening in the growth mask, a six-sided steeple-shaped n-type GaN layer is selectively grown, which has inclined crystal planes each composed of a plurality of crystal planes inclined from the major surface of the sapphire substrate by  
10 different angles of inclination to exhibit a convex plane as a whole. On the n-type GaN layer, an active layer and a p-type GaN layer are grown to make a light emitting element structure. Thereafter, a p-side electrode and an n-side electrode are formed.

15